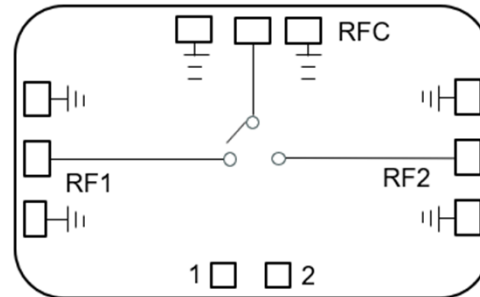


Features

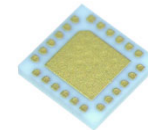
- SP2T Absorptive design
- Frequency:DC-20GHz
- Isolation: 50dB
- Insertion Loss: 1.2dB
- Return Loss (ON):18dB
- Control Voltage:0/-5V
- Switching Speed:15ns
- Die Size: 1.5x1.5x 0.1 mm



- QFN package available 4x4 mm

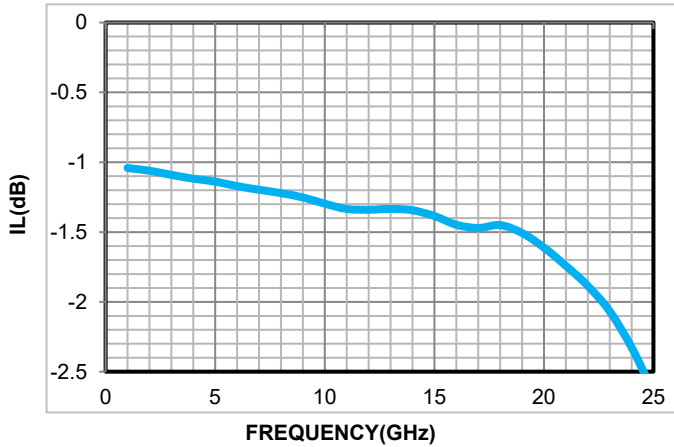
Typical Applications

- Voltage control no current
- Fast Switching Speed
- Low Insertion Loss and High Isolation
- Customization available upon request

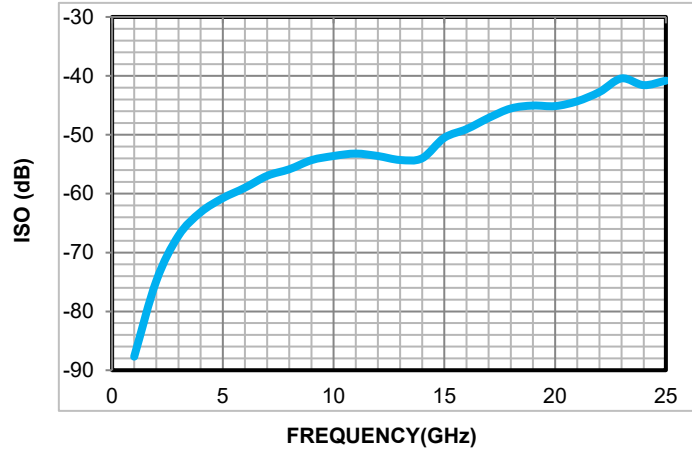

Electrical Specifications
TA = +25°C

Parameters	Min.	Typ.	Max.	Min.	Typ.	Max.	Units
Frequency	DC-6		6-20				GHz
Insertion Loss		1.2	1.5		1.4	1.7	dB
Isolation	55	65		40	50		dB
Return Loss (ON State)	18	20		18	22		dB
Output Return Loss (OFF State)	18	19		18	20		dB
Input P-1		18			18		dBm
RF Input power			30			30	dBm
IIP3		28			28		dBm
Switching Speed	15						ns

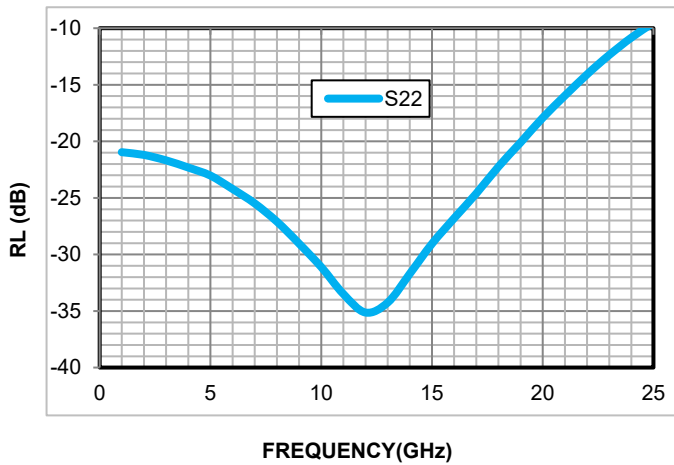
Insertion Loss vs. Frequency



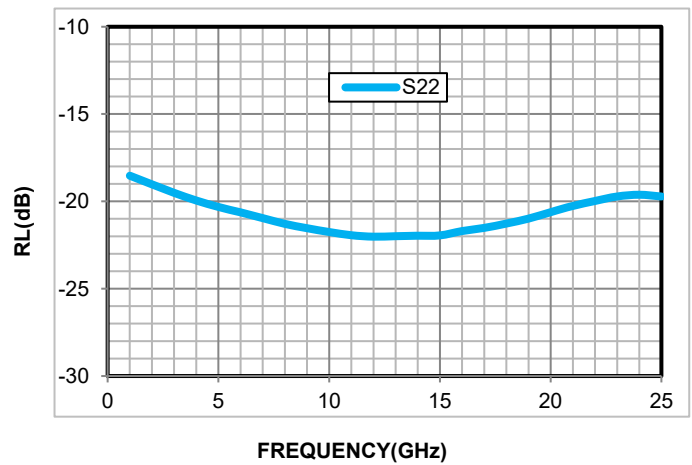
Isolation vs. Frequency



RL-On vs. Frequency



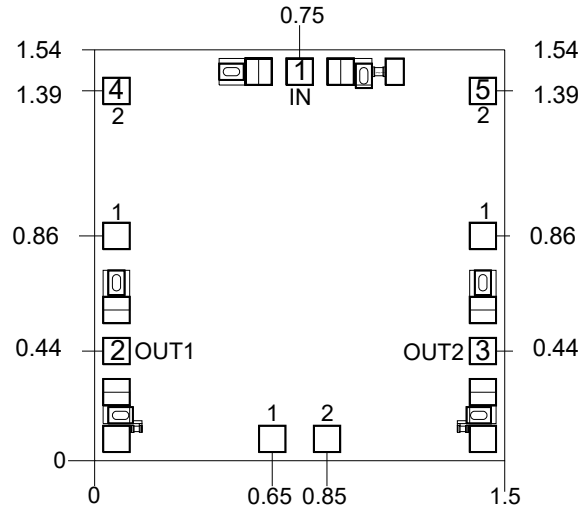
RL-Off vs. Frequency





Outline Drawing:

All Dimensions in mm



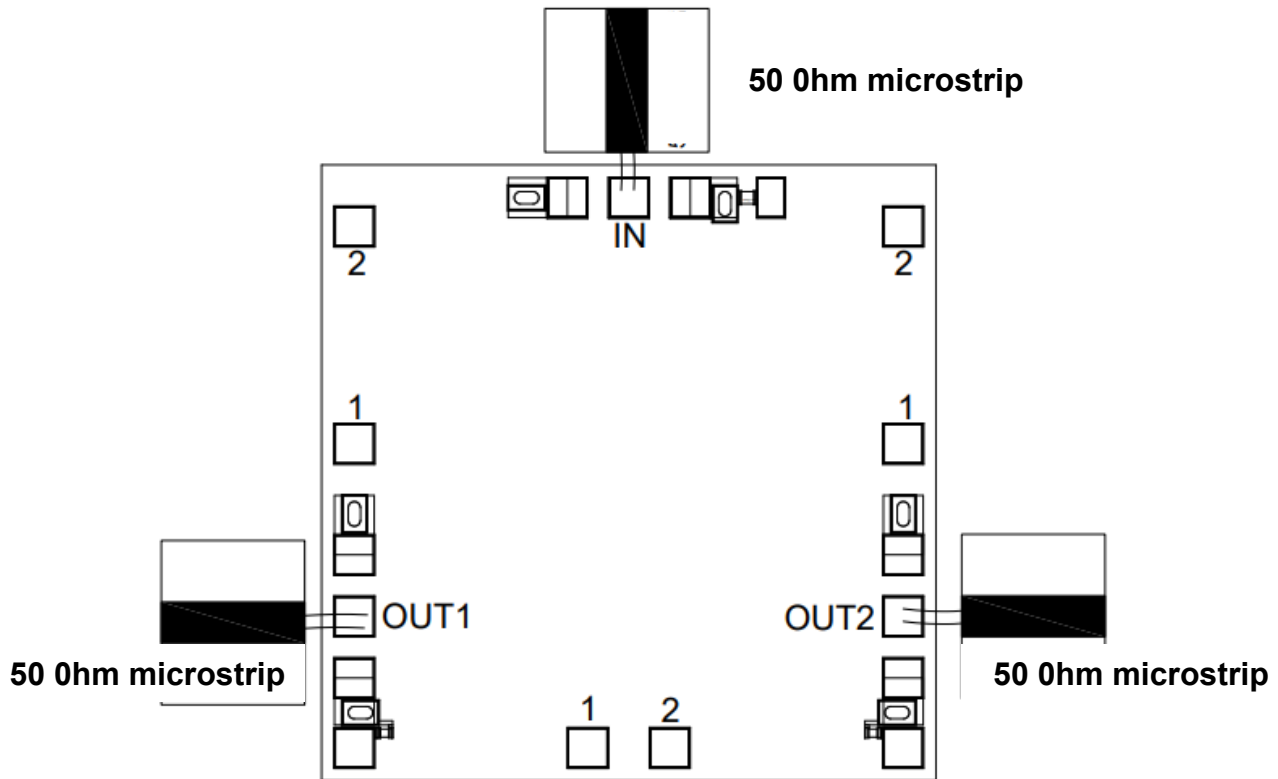
True Table

Ctrl (V)		Status	
1	2	IN-OUT1	IN-OUT2
0	-5	ON	OFF
-5	0	OFF	ON

Pad	Function	Description
1,2,3	IN, OUT	50 ohm circuit matched, and there is no blocking capacitor integrated inside the chip
4,5	Vctrl	Control Voltage
Bottom of chip	GND	The bottom of the chip should be in good contact with the RF and DC ground



Assembly Drawing



Notes:

1. Die thickness: 100um
2. Typical bond pad is 100*100 μm^2
3. Bond pad metalization: Gold
4. Backside metalization: Gold
5. Backside of the die (GND)
6. No connection required for unlabeled bond pads

Maximum Ratings:

1. RF input power: +30dBm
2. Control Voltage: -8~+1V
3. Storage temperature: -65°C to +150°C
4. Operating temperature: -55°C to 125°C